

IN THE SPECIFICATION

Please replace the paragraph beginning at page 21, line 11, with the following rewritten paragraph:

In the embodiments, a GaAlAs based material is used for a material to collect a light beam of a 0.8 to 0.9 micron short wavelength band, because absorption or transmission of a light beam in a material depends on whether the wavelength of the light beam is longer or shorter than the wavelength corresponding to the band gap of the material. Such a material as InAlAs, InAlP or InGaP may be used in place of the GaAlAs based material as a material to avoid restriction by band gap. A compound may be used for light collecting layer 27, which is expressed as $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{As}_z\text{P}_{1-z}$ ($0 \leq x, y, x+y, z \leq 1$) $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{As}_z\text{P}_{1-z}$ ($0 \leq x, y, x+y, z \leq 1$) combining at least one of Group 3 elements comprising Al, Ga and In and at least one of Group 5 elements comprising As and P.